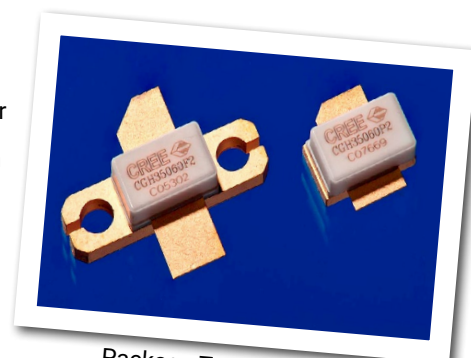


CGH35060F2 / CGH35060P2

60 W, 3100-3500 MHz, 28V, GaN HEMT

Cree's CGH35060F2/P2 is a gallium nitride (GaN) high electron mobility transistor (HEMT) designed specifically for high efficiency, high gain and wide bandwidth capabilities, which makes the CGH35060F2 / P2 ideal for 3.1-3.5 GHz S-band pulsed amplifier applications. The transistor is supplied in a ceramic/metal flange and pill package.



Package Type: 440193 & 440206
PN: CGH35060F2 & CGH35060P2

Typical Performance Over 3.1-3.5 GHz ($T_c = 25^\circ\text{C}$) of Demonstration Amplifier

Parameter	3.1 GHz	3.3 GHz	3.5 GHz	Units
Small Signal Gain	12.0	13.2	11.5	dB
$P_{OUT} @ P_{IN} = 36.5 \text{ dBm}$	47.0	47.6	46.7	dBm
$P_{OUT} @ P_{IN} = 36.5 \text{ dBm}$	10.4	11.06	10.1	dBm
Drain Efficiency @ $P_{IN} = 36.5 \text{ dBm}$	55.0	62.0	62.0	%
Input Return Loss	-7.3	-17.0	-4.3	dB

Note:

Measured in the CGH35060F2-AMP1 amplifier circuit, under 100 μsec Pulse Width, 20% Duty Cycle and 28 V.

Features

- 3.1 - 3.5 GHz Operation
- 60 W Peak Power Capability
- 12 dB Small Signal Gain
- 60 % Drain Efficiency



Large Signal Models Available for ADS and MWO

Absolute Maximum Ratings (not simultaneous) at 25°C Case Temperature

Parameter	Symbol	Rating	Units	Conditions
Drain-Source Voltage	V_{DS}	125	Volts	25°C
Gate-to-Source Voltage	V_{GS}	-10, +2	Volts	25°C
Power Dissipation	P_{DISS}	57.6	Watts	
Storage Temperature	T_{STG}	-55, +150	°C	
Operating Junction Temperature	T_J	225	°C	
Maximum Forward Gate Current	I_{GMAX}	14.4	mA	25°C
Maximum Drain Current ¹	I_{DMAX}	6	A	25°C
Soldering Temperature ²	T_S	245	°C	
Screw Torque	τ	80	in-oz	
Thermal Resistance, Junction to Case, Pulsed ³	$R_{\theta JC}$	1.67	°C/W	85°C, Pulse Width = 300%, Duty Cycle = 10%
Thermal Resistance, Junction to Case, CW ³	$R_{\theta JC}$	2.45	°C/W	85°C, Pulse Width = 300%, Duty Cycle = 10%
Case Operating Temperature ³	T_C	-40, +150	°C	

Note:

¹ Current limit for long term, reliable operation.

² Refer to the Application Note on soldering at <http://www.cree.com/rf/document-library>

³ Measured for the CGH35060F2 at $P_{DISS} = 57.6$ W

Electrical Characteristics ($T_C = 25^\circ\text{C}$)

Characteristics	Symbol	Min.	Typ.	Max.	Units	Conditions
DC Characteristics¹						
Gate Threshold Voltage	$V_{GS(th)}$	-3.8	-3.0	-2.3	V _{DC}	$V_{DS} = 10$ V, $I_D = 14.4$ mA
Gate Quiescent Voltage	$V_{GS(Q)}$	—	-2.7	—	V _{DC}	$V_{DS} = 28$ V, $I_D = 200$ mA
Saturated Drain Current	I_{DS}	11.6	14.0	—	A	$V_{DS} = 6.0$ V, $V_{GS} = 2$ V
Drain-Source Breakdown Voltage	V_{BR}	120	—	—	V _{DC}	$V_{GS} = -8$ V, $I_D = 14.4$ mA
RF Characteristics^{2,3} ($T_C = 25^\circ\text{C}$, $F_0 = 3.3$ GHz unless otherwise noted)						
Small Signal Gain	G_{SS}	10.0	13.0	—	dB	$V_{DD} = 28$ V, $I_{DQ} = 200$ mA
Drain Efficiency ⁴	η	40	62	—	%	$V_{DD} = 28$ V, $I_{DQ} = 200$ mA, $P_{IN} = 36.5$ dBm
Power Output ⁴	P_{OUT}	45.4	47.6	—	dBm	$V_{DD} = 28$ V, $I_{DQ} = 200$ mA, $P_{IN} = 36.5$ dBm
Output Mismatch Stress	VSWR	—	—	10:1	Ψ	No damage at all phase angles, $V_{DD} = 28$ V, $I_{DQ} = 200$ mA, $P_{OUT} = 60$ W Pulsed
Dynamic Characteristics						
Input Capacitance	C_{GS}	—	19.0	—	pF	$V_{DS} = 28$ V, $V_{GS} = -8$ V, $f = 1$ MHz
Output Capacitance	C_{DS}	—	5.9	—	pF	$V_{DS} = 28$ V, $V_{GS} = -8$ V, $f = 1$ MHz
Feedback Capacitance	C_{GD}	—	0.8	—	pF	$V_{DS} = 28$ V, $V_{GS} = -8$ V, $f = 1$ MHz

Notes:

¹ Measured on wafer prior to packaging.

² Measured in the CGH35060F2-AMP1 test fixture.

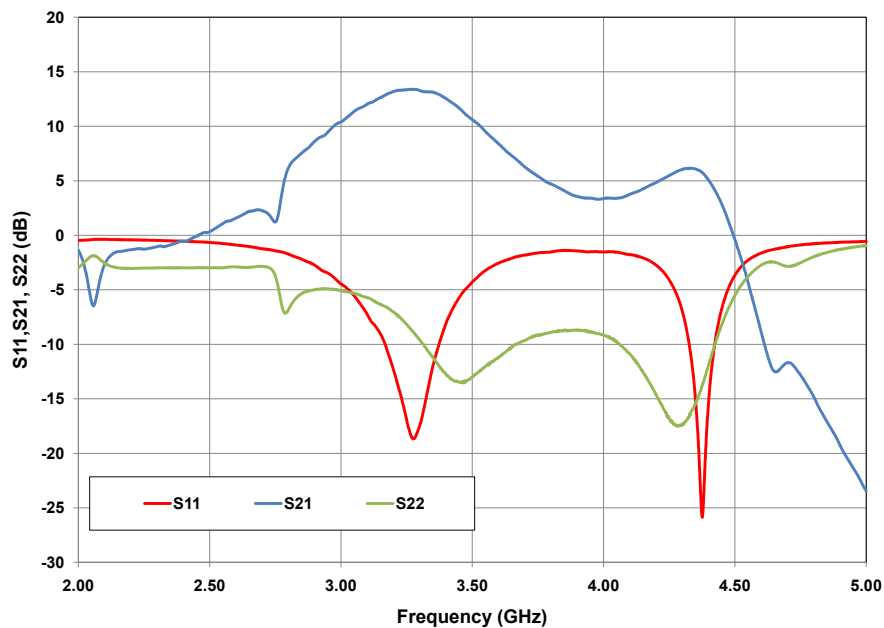
³ 100 μ S Pulse Width at 20% Duty Cycle.

⁴ Drain Efficiency = P_{OUT} / P_{DC} .

Typical Performance

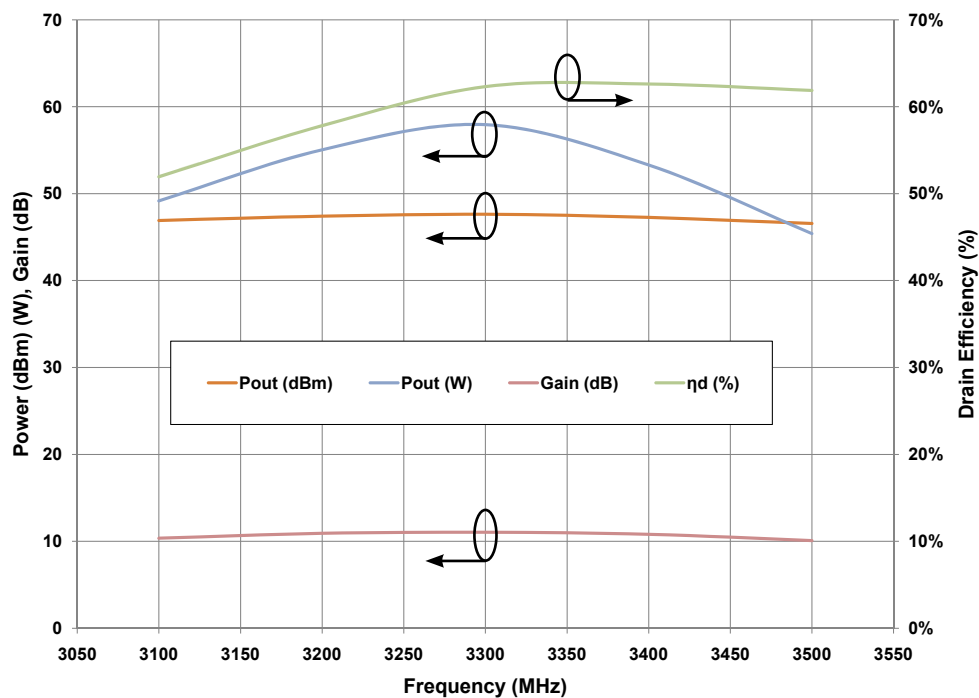
Small Signal Gain and Return Losses vs Frequency of the CGH35060F2 and CGH35060P2

$V_{DD} = 28\text{ V}$, $I_{DQ} = 200\text{ mA}$

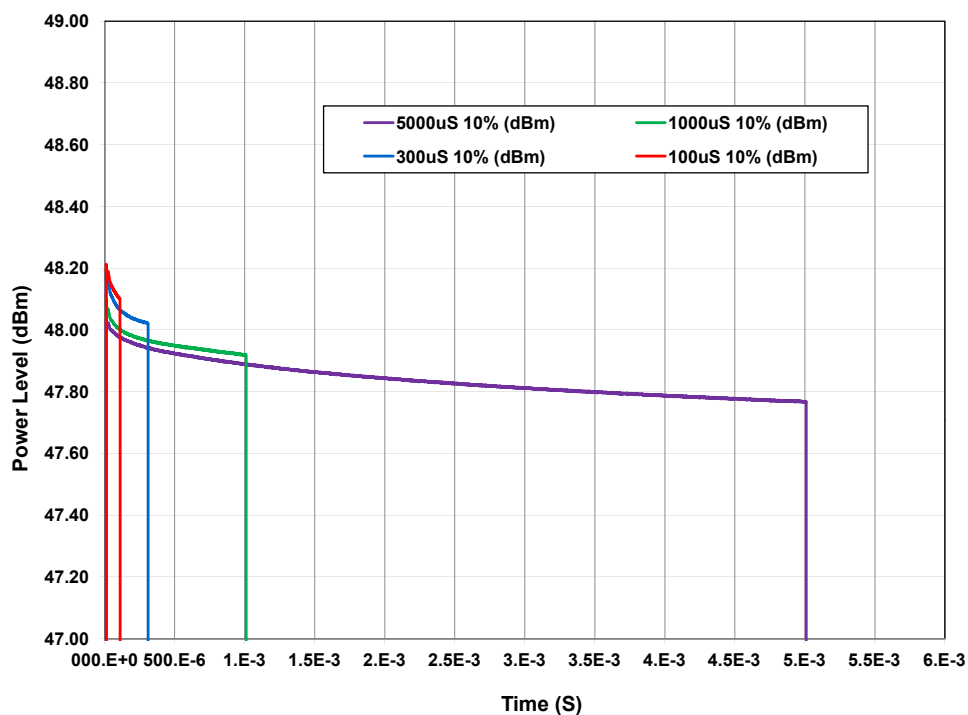


Output Power, Gain and Drain Efficiency vs Frequency of the CGH35060F2 and CGH35060P2

$V_{DD} = 28\text{ V}$, $I_{DQ} = 200\text{ mA}$, Pulse Width = 100 μsec , Duty Cycle = 20%



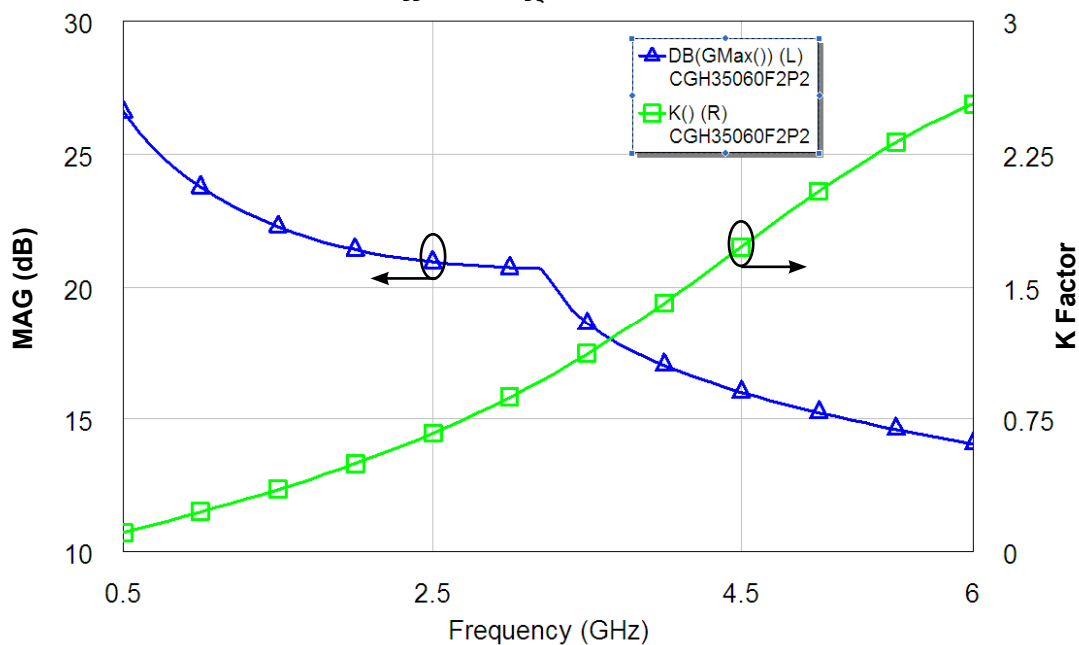
Typical Pulse Droop Performance



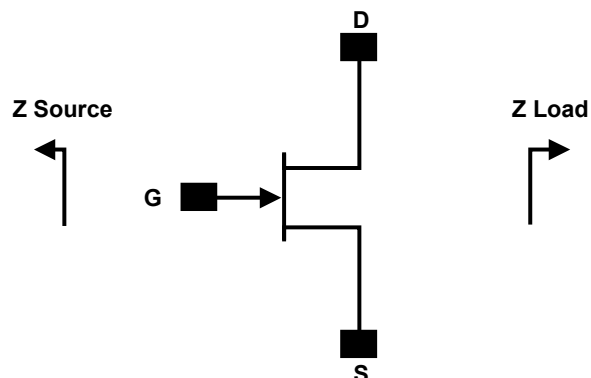
Typical Performance Data

Simulated Maximum Available Gain and K Factor of the CGH35060F2 and CGH35060P2

$V_{DD} = 28 \text{ V}$, $I_{DQ} = 200 \text{ mA}$



Source and Load Impedances



Frequency (MHz)	Z Source	Z Load
3100	3.6 -j13.5	8.0 -j8.5
3200	3.6 -j12.8	7.1 -j7.7
3300	3.5 -j12.1	6.5 -j6.8
3400	3.5 -j11.4	6.0 -j5.9
3500	3.3 -j10.7	5.6 -j5.1

Note¹: $V_{DD} = 28V$, $I_{DQ} = 200mA$. In the 440193 package.

Note²: Impedances are extracted from the CGH35060F2-AMP1 demonstration circuit and are not source and load pull data derived from the transistor.

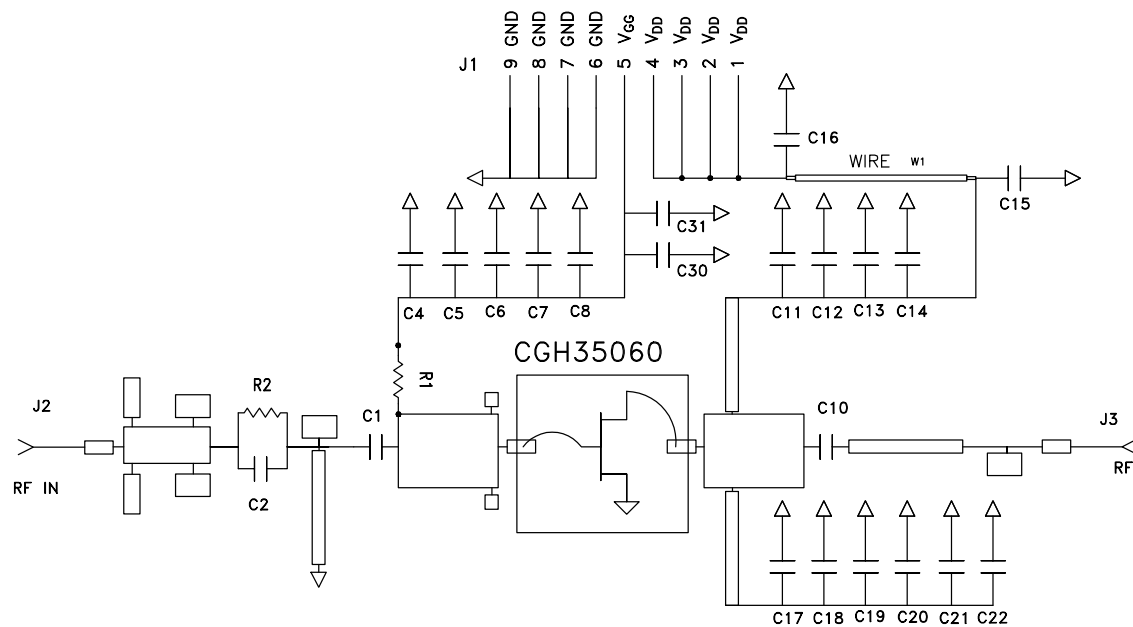
Electrostatic Discharge (ESD) Classifications

Parameter	Symbol	Class	Test Methodology
Human Body Model	HBM	1A (> 250 V)	JEDEC JESD22 A114-D
Charge Device Model	CDM	II (200 < 500 V)	JEDEC JESD22 C101-C

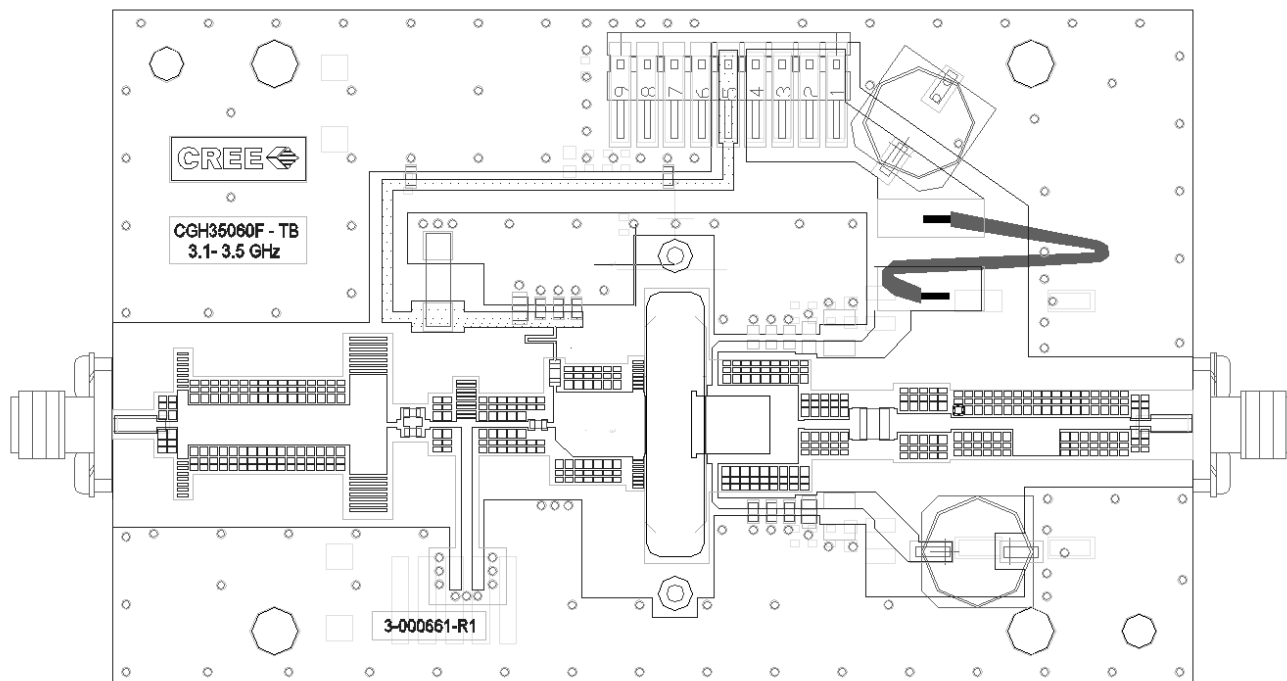
CGH35060F2-AMP1 Demonstration Amplifier Circuit Bill of Materials

Designator	Description	Qty
R1	RES, 1/16 W, 0603, 1%, 5.1 OHMS	1
R2	RES, 1/16 W, 0603, 1%, 100 OHMS	1
C6,C13,C19	CAP, 470 pF, +/-5%, 100 V, 0603	3
C16,C22	CAP, 33 uF 100 V ELECT FK SMD	2
C15,C21	CAP CER 1.0 uF, 100 V, 10%, X7R 1210	2
C8	CAP 10 uF 16V SMT TANTALUM	1
C10	CAP, 20.0 pF, +/-5%, 0603, ATC 100B	1
C1	CAP, 5.1 pF, +/-5%, 0603, ATC 600S	1
C2	CAP, 3.0 pF, +/-0.1 pF, 0603, ATC 600S	1
C5,C12,C18,C30,C31	CAP, 4.7 pF, 5% pF, 0603, ATC	5
C4,C11,C17	CAP, 7.5 pF, 0.1 pF, 0603, ATC	3
C7,C14,C20	CAP CER 33000 pF, 0805, 100V, X7R	3
	PCB	1
	BASEPLATE	1
	PRESSPLATE	1
J2,J3	CONN, SMA, PANEL MOUNT JACK	2
J1	HEADER RT>PLZ .1CEN LK 9POS	1
	2-56 SOC HD SCREW 1/4 SS	4
	#2 SPLIT LOCKWASHER SS	4
W1	WIRE, BLACK, 22 AWG ~ 2.0"	1

CGH35060F2-AMP1 Demonstration Amplifier Circuit Schematic



CGH35060F2-AMP1 Demonstration Amplifier Circuit Outline

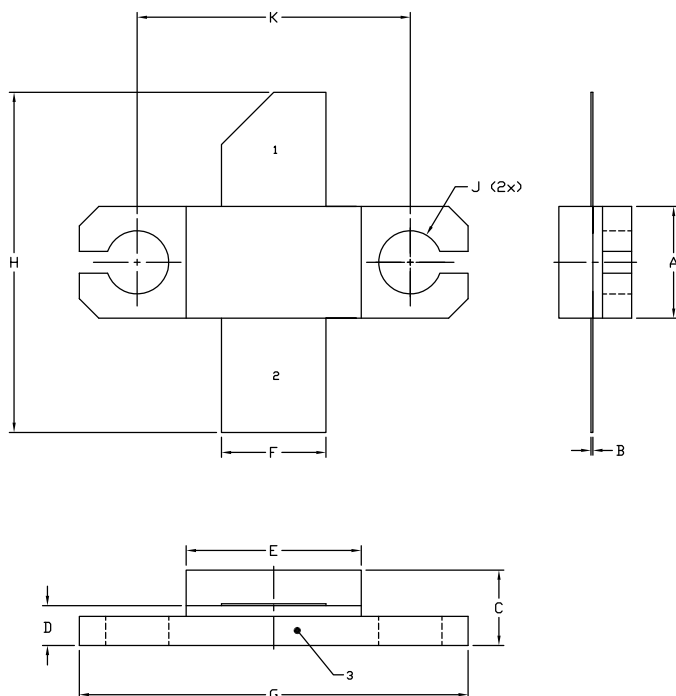


Typical Package S-Parameters for CGH35060F2/P2
 (Small Signal, $V_{DS} = 28 \text{ V}$, $I_{DQ} = 200 \text{ mA}$, angle in degrees)

Frequency	Mag S11	Ang S11	Mag S21	Ang S21	Mag S12	Ang S12	Mag S22	Ang S22
500 MHz	0.927	-170.09	7.16	79.27	0.016	-6.59	0.596	-168.07
600 MHz	0.928	-172.55	5.95	75.10	0.016	-9.91	0.605	-168.34
700 MHz	0.929	-174.46	5.08	71.25	0.015	-12.90	0.615	-168.44
800 MHz	0.930	-176.04	4.42	67.64	0.015	-15.66	0.626	-168.49
900 MHz	0.931	-177.39	3.91	64.20	0.015	-18.24	0.637	-168.54
1.0 GHz	0.932	-178.59	3.50	60.90	0.015	-20.65	0.648	-168.63
1.1 GHz	0.933	-179.70	3.16	57.72	0.015	-22.94	0.659	-168.78
1.2 GHz	0.935	179.27	2.88	54.66	0.014	-25.10	0.670	-168.99
1.3 GHz	0.936	178.29	2.65	51.70	0.014	-27.14	0.681	-169.25
1.4 GHz	0.937	177.34	2.45	48.83	0.014	-29.08	0.692	-169.58
1.5 GHz	0.938	176.41	2.28	46.04	0.013	-30.91	0.702	-169.96
1.6 GHz	0.939	175.49	2.13	43.33	0.013	-32.65	0.712	-170.40
1.7 GHz	0.940	174.57	2.00	40.70	0.013	-34.29	0.721	-170.87
1.8 GHz	0.941	173.65	1.88	38.13	0.013	-35.85	0.730	-171.39
1.9 GHz	0.942	172.73	1.78	35.62	0.012	-37.32	0.738	-171.94
2.0 GHz	0.943	171.79	1.69	33.16	0.012	-38.70	0.746	-172.53
2.1 GHz	0.943	170.83	1.62	30.76	0.012	-40.01	0.753	-173.14
2.2 GHz	0.944	169.85	1.55	28.40	0.012	-41.25	0.760	-173.78
2.3 GHz	0.944	168.85	1.49	26.07	0.012	-42.41	0.766	-174.44
2.4 GHz	0.944	167.82	1.44	23.78	0.011	-43.51	0.772	-175.12
2.5 GHz	0.945	166.75	1.39	21.52	0.011	-44.55	0.777	-175.82
2.6 GHz	0.944	165.64	1.35	19.27	0.011	-45.52	0.781	-176.54
2.7 GHz	0.944	164.49	1.32	17.03	0.011	-46.44	0.785	-177.27
2.8 GHz	0.944	163.29	1.29	14.80	0.011	-47.31	0.789	-178.03
2.9 GHz	0.943	162.03	1.26	12.57	0.011	-48.13	0.792	-178.80
3.0 GHz	0.943	160.71	1.24	10.34	0.010	-48.92	0.795	-179.59
3.2 GHz	0.941	157.85	1.22	5.80	0.010	-50.38	0.798	178.78
3.4 GHz	0.938	154.62	1.21	1.13	0.010	-51.75	0.800	177.06
3.6 GHz	0.934	150.94	1.21	-3.76	0.010	-53.09	0.800	175.23
3.8 GHz	0.928	146.65	1.24	-8.97	0.010	-54.51	0.798	173.28
4.0 GHz	0.921	141.58	1.28	-14.63	0.011	-56.12	0.794	171.18
4.2 GHz	0.911	135.46	1.35	-20.90	0.011	-58.11	0.787	168.89
4.4 GHz	0.897	127.93	1.45	-28.01	0.012	-60.71	0.777	166.35
4.6 GHz	0.880	118.44	1.57	-36.26	0.012	-64.27	0.764	163.51
4.8 GHz	0.857	106.23	1.73	-46.04	0.014	-69.22	0.746	160.26
5.0 GHz	0.828	90.20	1.93	-57.83	0.015	-76.13	0.723	156.46
5.2 GHz	0.796	69.08	2.15	-72.17	0.017	-85.57	0.692	151.91
5.4 GHz	0.770	42.01	2.35	-89.39	0.018	-97.96	0.649	146.29
5.6 GHz	0.766	10.14	2.48	-109.22	0.019	-113.08	0.590	139.24
5.8 GHz	0.793	-22.34	2.47	-130.55	0.020	-129.85	0.509	130.26
6.0 GHz	0.839	-50.86	2.33	-152.01	0.019	-146.93	0.401	118.41

To download the s-parameters in s2p format, go to the [CGH35060F2/P2 Product Page](#), click on the documentation tab.

Product Dimensions CGH35060F2 (Package Type – 440193)



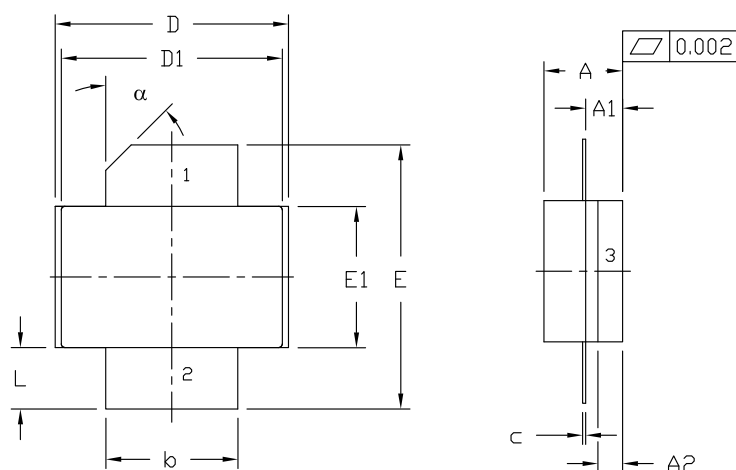
NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1992.
2. CONTROLLING DIMENSION: INCH.
3. ADHESIVE FROM LID MAY EXTEND A MAXIMUM OF 0.020" BEYOND EDGE OF LID.
4. LID MAY BE MISALIGNED TO THE BODY OF THE PACKAGE BY A MAXIMUM OF 0.008" IN ANY DIRECTION.
5. ALL PLATED SURFACES ARE Ni/AU.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.225	0.235	5.72	5.97
B	0.004	0.006	0.10	0.15
C	0.145	0.165	3.68	4.19
D	0.077	0.087	1.96	2.21
E	0.355	0.365	9.02	9.27
F	0.210	0.220	5.33	5.59
G	0.795	0.805	20.19	20.45
H	0.670	0.730	17.02	18.54
J	Ø .130		3.30	
k	0.562		14.28	

PIN 1. GATE
PIN 2. DRAIN
PIN 3. SOURCE

Product Dimensions CGH35060P2 (Package Type – 440206)



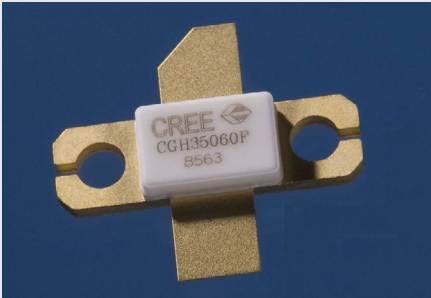
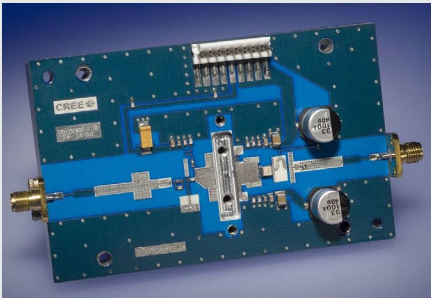
NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M - 1994.
2. CONTROLLING DIMENSION: INCH.
3. ADHESIVE FROM LID MAY EXTEND A MAXIMUM OF 0.020" BEYOND EDGE OF LID.
4. LID MAY BE MISALIGNED TO THE BODY OF PACKAGE BY A MAXIMUM OF 0.008" IN ANY DIRECTION.

DIM	INCHES		MILLIMETERS		NOTES
	MIN	MAX	MIN	MAX	
A	0.125	0.145	3.18	3.68	
A1	0.057	0.067	1.45	1.70	
A2	0.035	0.045	0.89	1.14	
b	0.210	0.220	5.33	5.59	2x
c	0.004	0.006	0.10	0.15	2x
D	0.375	0.385	9.53	9.78	
D1	0.355	0.365	9.02	9.27	
E	0.400	0.460	10.16	11.68	
E1	0.225	0.235	5.72	5.97	
L	0.085	0.115	2.16	2.92	2x
α	45° REF		45° REF		

PIN 1. GATE
PIN 2. DRAIN
PIN 3. SOURCE

Product Ordering Information

Order Number	Description	Unit of Measure	Image
CGH35060F2	GaN HEMT (Flanged)	Each	
CGH35060P1	GaN HEMT (Pill)	Each	
CGH35060-TB	Test board without GaN HEMT	Each	
CGH35060F2-AMP	Test board with GaN HEMT installed	Each	

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